Timing Processor (LINE, FRAME, SMPS) for TV Sets

General Description

This integrated circuit uses I^2L bipolar technology and combines analog signal processing with digital processing. Timing signals are obtained from a Voltage-Controlled Oscillator (VCO) operating at 500 kHz by means of a cheap ceramic resonator. A chain of dividers and appropriate logic functions are producing very accurately defined sampling pulses and the necessary timing signals. This avoids the frequency adjustment normally required with line and frame oscillators.

Features

- 500 kHz VCO and appropriate logic avoids adjustment of timing pulses
- Identical line and Switch Mode Power Supply (SMPS) frequency avoids visible interference on screen
- Multistandard capability by automatic 50/60 Hz identification
- Low power dissipation by controlling a frame thyristor (or class D output transistor stage)
- Video identification circuit
- Super sandcastle

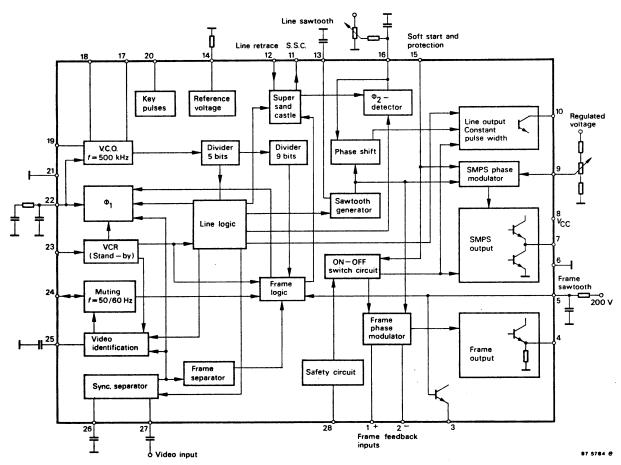


Figure 1. Block diagram

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Case: DIP 28

Absolute Maximum Ratings

 $T_{amb} = 25^{\circ}C$, unless otherwise specified.

Parameters		Symbol	Value	Unit
Supply voltage	Pin 8	VS	14	V
AGC current	Pin 20	I ₂₀	5	mA
Video identification current	Pin 24	I ₂₄	10	mA
Line retrace current	Pin 12	± I ₁₂	10	mA
Line output current	Pin 10	$+I_{10}$	40	
		-I ₁₀	10	
Frame sawtooth generator	Pin 3	IS	20	mA
Frame output current	Pin 4	I ₄	100	mA
SMPS output current	Pin 7	$\pm I_7$	50	mA
Safety input current	Pin 28	I ₂₈	5	mA
Safety input voltage	Pin 28	V ₂₈	V _{CC}	
Ambient temperature range		T _{amb}	0 to +70	°C
Storage temperature range		T _{stg}	-25 to +150	°C

Thermal Resistance

Parameters	Symbol	Value	Unit
Junction ambient	R _{thJA}	55	K/W

Electrical Characteristics

 $V_S = V_{CC} = 12$ V, $T_{amb} = 25^{\circ}C$, unless otherwise specified

Parameters	Test Conditions / Pins	Symbol	Min.	Тур.	Max.	Unit
Supply current	Frame, line and SMPS output without load Pin 8	I _S		60	80	mA
Sync. separator Pins 26 and 27						
Positive video input signal, ac coupled	Source impedance Pin 27 $\leq 200 \Omega$	V ₂₇	0.2	1.8	3	V _{pp}
Negative clamping current during sync. pulse		-I ₂₇	25	40	55	μΑ
Clamping current, continuously		I ₂₇	3	5	9	μΑ
Slicing level decoupling	Negative current Pin 26	-I ₂₆		640	1000	μA
50 % of sync. amplitude	Positive current	I ₂₆	12	25	36	μΑ
Pulse for keyed AGC	Pin 20			•		
Output current		I ₀			5	mA
Output separation voltage	$I_0 = 5 \text{ mA}$	V ₀			0.4	V
Delay time from the key puls middle of the sync. pulse	se leading edge to the	t _{d1}		3.4		μs
Delay time from the middle pulse trailing	of the sync. pulse to the key	t _{d2}		4.8		μs

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Parameters	Test Conditions / Pi	ns	Symbol	Min.	Тур.	Max.	Unit
Voltage control oscillator,	VCO P	in 17, 1	8, 19				
$V_{S} = V_{CC} = 11 \text{ V to } 13 \text{ V}$	Ceramic resonator type	e: CSB	503 B				
Operating voltage	Р	in 8	Vs	5		13.2	V
Frequency control range	Low-end		flow		15.3		kHz
after H. divider	High-end		f _{high}		16.1		
Control current	Р	in 22	$\pm I_{22}$			10	μΑ
Phase detector \emptyset_1	P	in 22					
Output current	Low loop gain		$\pm I_0$	0.35	0.5	0.65	mA
	High loop gain			1	1.5	2	
Ratio of charging and			I _{ch} /I _{dis}		1		
discharging current							
Transfer gain	Low loop gain		G _{TL}		1.2		kHz/µs
	High loop gain		G _{TH}		3.6		
Window pulse width			tØ1		10		μs
(only in low loop gain, vide							
Delay time between middle	of key pulse and $\emptyset_1 \operatorname{com}$	par-	t _d		0		μs
ison edge							
VCR and STAND-BY swi		in 23				1	-
Threshold voltage VCR (V	CR switch is in ON positi	ion	V _T	1.6	2.1	2.6	V
below this value)	DU					1.0	
Threshold voltage STAND-		1	V_{T}	3.2	4	4.8	V
(STAND-BY switch is in O	N position above this lev	(el)	-	0.000			
Input current			-I ₁	0.030		1	mA
Video identification, see fi	-	ins 24 a					1 .
Input current		in 24	II			10	mA
Output saturation voltage	$I_I = 5 \text{ mA}, \text{ no video sig}$		V _{Osat}			0.6	V
Output voltage	· · · · · · · · · · · · · · · · · · ·	in 24	V_0	5.5	6	7.5	V
	$I_{i(Video)} = 2.5 \text{ mA}$						
Input current		in 24	II			10	μΑ
Output current,	Р	'in 25	I _{ch}	0.5	0.75	1	mA
charging the capacitor							
Ratio between the charg-		'in 25	I _{ch} /I _{dis}	1.7		4.0	
ing and discharging current							
Identification sampling	Р	'in 25	t ₂₅	1.3		2.2	μs
time							
Threshold voltage		in 25				_	
	lower to higher value		V_{T}	4	4.5	5	V
TT 1	(low means no video)		* *				
Hysteresis voltage		'in 25	V _{hyst}		350		mV
H. ramp generator, see fig		in 13		-		· .	
Saw-tooth amplitude	peak to peak		v	3	3.5	4	V
synchronized state			т	107	200	015	
Charge current			I _{ch}	185	200	215	μΑ
Saw-tooth base voltage			V _{min}			0.5	V
Discharging time			t _{dis}			4	μs
Delay time between \emptyset_2 com	paring edge and leading		td		1.95		μs
edge of discharging pulse							

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Parameters	Test Conditions / Pins	Symbol	Min.	Тур.	Max.	Unit
Super sandcastle, SSC	Pin 11					
Output current		I ₁₁	-10		+ 10	mA
Output voltage levels;	$I_{11} = 5 \text{ mA}$					
Burst key pulse		V _{Burst}	9			V
Horizontal blank pulse		V _{HB}	4	4.5	5	
Frame blank pulse	$I_{11} = 5mA$ frame out of function	V _{VB}	2	2.5	3	V
Delay time between middle of leading edge of burst key put		t _d	2.3		3	μs
Duration of burst key pulse			3.7	4	5	μs
Delay time	between SSC cutting level at pin 12 and line blank pulse	t _d			0.5	μs
Frame retrace blanking duration				24		lines
Line retrace input	Pin 12					
First threshold for blanking	1 111 12	V _b	11		12	V
Second threshold for \emptyset_2		$V_{\emptyset 2}$	-1	1.3	2.3	V V
Input currents:	V ₁₂ =12 V	ν _{ψ2} I ₁₂	-1	550	2.5	μΑ
input currents.	$V_{12} = 5 V$	112		200		μΑ
	$V_{12} = 0 V$			-50		μΑ
	$V_{12} = 1 V$		-2	-1		mA
Operating input voltage		-V ₁₂			1	V
Phase detector Ø2,	Pin 16					
Charging current		I _{ch}	0.4	0.6	0.8	mA
Ratio of charging and discharging current		I _{ch} /I _{dis}		1		
Delay time between the com f_0 (VCO) = 500 kHz	paring edges of \emptyset_1 and \emptyset_2	t _d	1.5	2	2.8	μs
Input current of internal erro shift	r amplifier for \emptyset_2 phase	I ₁₆			3	μΑ
Time difference between \emptyset_2 of line retrace (without exter		Δt		0		μs
Horizontal output (Open co		1			1	
Output saturation voltage	$I_0 = 20 \text{ mA}$	V ₀			1	V
Output saturation voltage		I ₀			40	mA
Output current Output pulse duration	$f_0 = 500 \text{ kHz}$	t _p	24	26	28	μs
\emptyset_2 phase range	without external phase	t _Ø	14	16	19	μs μs
by phase range	shift	40	14	10	17	μο
Frame logic	I	· · · · ·		1		1
Free running period video identification = 0		N		315		lines
Search window		N	247		361	lines
50 Hz window		N	309		315	lines
60 Hz window		N	247		277	lines
VCR mode window		N	247		361	lines
Frame saw-tooth generator	1	Pin 5		1	1	1

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Parameters	Test Conditions / Pins	Symbol	Min.	Тур.	Max.	Unit
Saw-tooth amplitude	peak to peak	v	2	3	4	V
60 Hz internal current generator		Io	12	14	16	μΑ
Discharge time	$C = 0.47 \ \mu F, \ \Delta V_C = 4 \ V$	t _{dis}			70	μs
Delay time	between beginning of dis- charging and leading edge of the first main equaliz- ing pulse which appears during internal sync. pulse			5		μs
Saw tooth base voltage	$I_3 = 0.to \ 10 \text{ mA}$ Pin 3	V _{min}	1	1.26	1.4	V
Frame feed back inputs	Pins	1 and 2				
Input current		I _{1,2}			10	μΑ
Common mode range		CMR	2		10	V
Frame output, see figure 4	Pin 4					
Operating output current		-I ₀			80	mA
Limit value		-I _{0M}			100	mA
Max. "ON" time		ton		40		μs
Output phase range		tø	0		t _{onmax}	μs
Negative over current	limit value	I _{N0}		10		mA
Output voltage	$I_4 = -80 \text{ mA}$	Vo	10			V
Switch mode power supply	, SMPS					
Input current	Pin 9	II			10	μΑ
Internal reference voltage		V _{ref}	1.2	1.26	1.35	V
SMPS Output, see figure 5	Pin 7					
Output current limit value		I ₀	-50		50	mA
Output voltage	$I_0 = -20 \text{ mA}$ $I_0 = +20 \text{ mA}$	V ₀	10		2	V
t _{on} time		t _{onmax}	27	28	29	μs
Position of trailing edge of SMPS pulse				before midd H sync. puls		
Negative over current limit v	value	I _{NO}			50	mA
Safety input,	Pin 2	8				
Threshold voltage		VT	1.15	1.26	1.37	V
Input current	$V_T = V_{ref}$	II			3	μΑ
Input voltage		V _{28max}			V _{CC}	
Soft starting input and SMI	$PS - \overline{T_{ON}}$ limitation (see f		5			
Charging current	$t = 4 \ \mu s$	I _{ch}	70		130	μΑ
Ratio of charging and discharging current		I _{ch} / I _{dis}		1		
Charging time		t _{ch}		4		μs
Ratio of charging and dis- charging time		t _{ch} /t _{dis}		2		

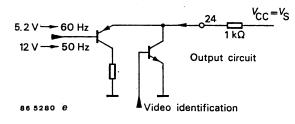
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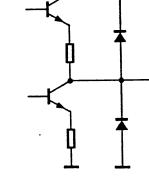
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Parameters	Test Conditions / Pins	Symbol	Min.	Тур.	Max.	Unit
Switch-ON, Switch-OFF pr	rocessing Pins 4, 7	7 and 10				
SMPS	frame and line V _{CC} start- ing V _{CC} stopping	V _S	5.25 + V _{hyst} 5.25		6.5 + V _{hyst} 6.25	V
Hysteresis between switch on- and off level		V _{hyst}		500		mV
Voltage reference	Pin 14	V _{ref}	1.2	1.26	1.35	V





 $V_{CC} = V_S$



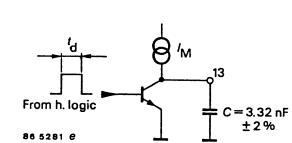
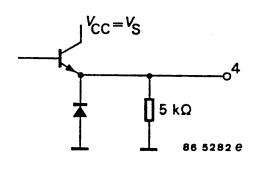


Figure 2.





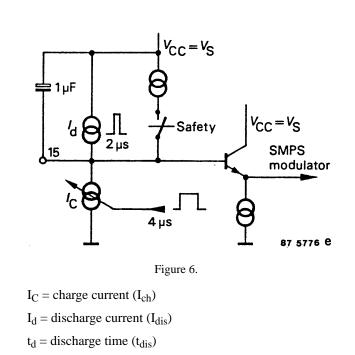


Figure 4.



Application

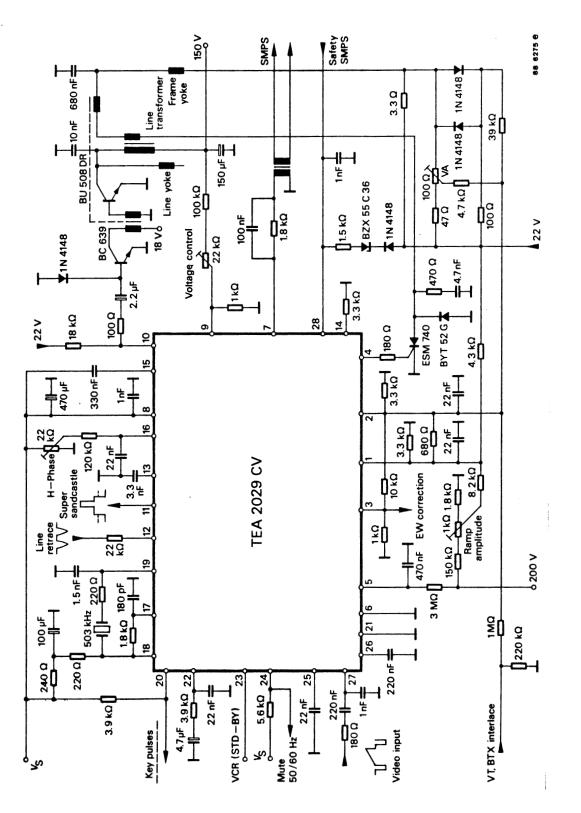


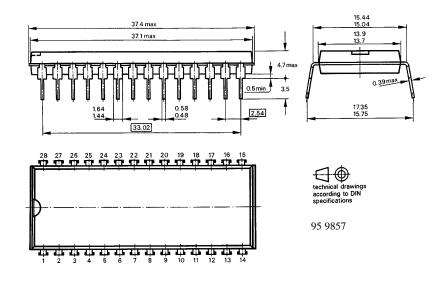
Figure 7.

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Dimension in mm

Package: DIP 28



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Ozone Depleting Substances Policy Statement

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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